

Abstract: We study the influence of temperature-induced structural lattice fluctuations on the elastic electron transport in single-wall carbon nanotubes within a density-functional-based scheme. In the linear response regime, the linear conductance is calculated via configurational averages over the distorted lattice. Results obtained from a frozen-phonon approach as well as from molecular dynamics simulations are compared. We further demonstrate that the **effect of structural fluctuations** can be approximately captured by the **Anderson model of disorder**. The influence of individual vibrational modes on the electronic transport is discussed as well as the role of **zero-point fluctuations (ZPF)**.

Landauer Conductance

Conductance $g \leftrightarrow$ Elastic-scattering problem \leftrightarrow Transmission probability $T(E)$

$$g = 2 \frac{e^2}{h} T(E_F)$$

$$H = H_l + H_M + V_{l,M}, \quad l = L, R$$

$$T = Tr_M[G_M^\dagger \Gamma_R G_M \Gamma_L]$$

G_M = Green function of the scattering region including coupling to the leads

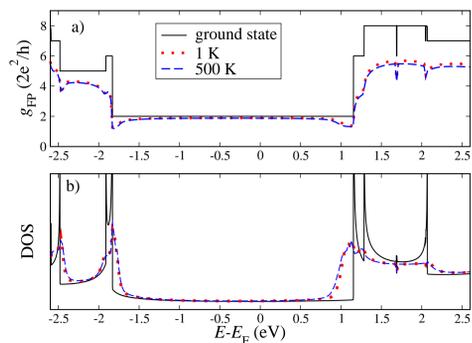
Γ_l = spectral density of l -lead

$$[(E + i0^+) \mathbf{1}_M - \mathbf{H}_M - \Sigma_L - \Sigma_R] \mathbf{G}_M = \mathbf{1}$$

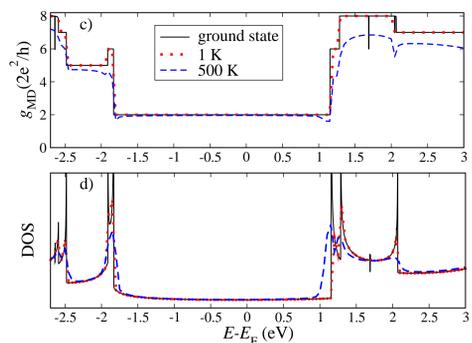
$$\Sigma_l = \mathbf{V}_{l,M}^\dagger \mathbf{G}_l \mathbf{V}_{l,M}$$

$$\Gamma_l = i[\Sigma_l(E + i0^+) - \Sigma_l(E + i0^-)]$$

FP- and MD-approaches



Average conductance in the **frozen-phonon** approach



Time-averaged conductance from **molecular dynamics** simulations

- **FPA** and **MD** yield similar results \rightarrow harmonic approximation works well for CNTs
- **Zero-point fluctuations** in the FPA induce sudden decrease of g_{FP} w.r.t. the static, ideal CNT conductance
- **Conductance dips** at the crossover points, where new bands start to contribute
- **Negligible influence** of structural fluctuations on the **massless linear bands** crossing the Fermi energy
- **Strong conductance suppression** on **higher-lying bands** related to band mixing

Configurational Averages [1]

- Density-functional-parametrized tight-binding approach to calculate the electronic and structural properties of the molecular junction
- Harmonic approximation for the lattice degrees of freedom, i.e.

$$H_{vib} = \sum_{\alpha=1}^{3N} \left(\frac{p_{\alpha}^2}{2m_{\alpha}} + \frac{m_{\alpha} \omega_{\alpha}^2 x_{\alpha}^2}{2} \right),$$

where m_{α} is the reduced mass of mode α , and ω_{α} the corresponding mode eigenfrequency. The frequencies ω_{α} and mode eigenvectors e_{α} are determined by diagonalization of the Hessian matrix.

- Thermal fluctuations** included in two complementary ways :

- frozen-phonon approach (FPA)**: the scattering region is distorted according to the phonon eigenvectors
- Molecular dynamics simulations (MD)**: the atoms on the scattering region evolve in time according to the classical dynamics of a system in contact with a thermal bath. The forces are calculated quantum mechanically, however.

- Average transmission probabilities:

- FP** calculations:

$$g_{FP} = g_0 \langle T(E) \rangle_{\alpha} = g_0 \int dx_1 dx_2 \dots dx_{3N} T(E; \{x_{\alpha}\}) P(\{x_{\alpha}\}),$$

$$P(\{x_{\alpha}\}) = \prod_{\alpha} \left(\frac{m_{\alpha} \omega_{\alpha}^2}{2\pi E_{\alpha}} \right)^{1/2} \exp\left(-\frac{m_{\alpha} \omega_{\alpha}^2 x_{\alpha}^2}{2E_{\alpha}}\right).$$

$P(\{x_{\alpha}\})$ is a product of gaussian distribution functions for the set of quasi-random numbers $\{x_{\alpha}\}$ and $E_{\alpha} = \hbar \omega_{\alpha} (N(\omega_{\alpha}) + 1/2)$ is the thermal energy of the α th oscillator.

- MD** simulations:

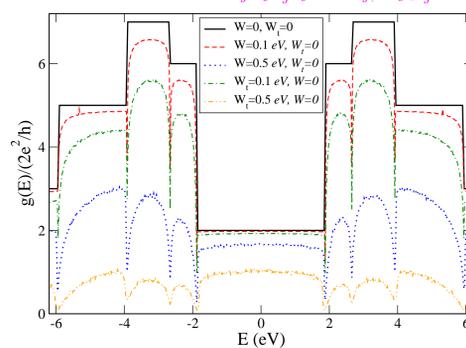
$$g_{MD} = \frac{2e^2}{h} \langle T(E) \rangle_{\tau} = \frac{1}{\tau} \int_0^{\tau} dt T(E, \tau)$$

[1] A. Pecchia et al., PRB 68 235321 (2003)

Static disorder

Effect of thermal fluctuations is qualitatively similar to Anderson disorder (see also Anantram/Govindan PRB 58 4882 (1998))

Anderson model: $H = \sum_j \epsilon_j c_j^\dagger c_j - \sum_{j,l} t_{lj} c_j^\dagger c_l + H.c.$

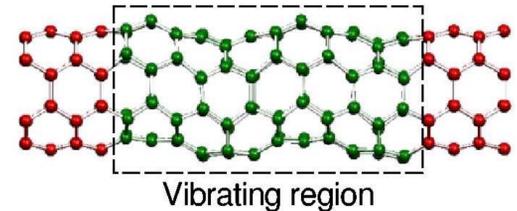


Average conductance obtained from the Anderson Hamiltonian. Results for both, onsite and off-diagonal disorder are shown.

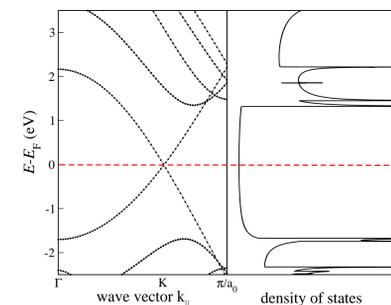
- Neglecting of ZP motion increases the weight of low-frequency modes; these modes are less effective in scattering electrons \rightarrow the global conductance change is less strong
- Thermal factors of high-frequency modes are basically negligible \rightarrow ZP motion is dominant for them

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Physical System: Metallic (4,4) CNT



Snapshot of the vibrating scattering region (green) of the CNT. The semiinfinite contacts (red) also consist of (4,4) tubes with a **fixed** geometry.



Electronic band structure and corresponding density of states (DOS) for the **perfect** infinite (4,4) CNT. $a_0 = 2.46 \text{ \AA}$ is the nanotube lattice constant.

Single-mode analysis: Role of zero-point (ZP) motion

